

Connecting via Winsock to STN

Welcome to STN International! Enter x:x

LOGINID:sssptal600LUE

PASSWORD:

TERMINAL (ENTER 1, 2, 3, OR ?):2

\* \* \* \* \* Welcome to STN International \* \* \* \* \*

NEWS	1		Web Page URLs for STN Seminar Schedule - N. America
NEWS	2		"Ask CAS" for self-help around the clock
NEWS	3	Feb 24	PCTGEN now available on STN
NEWS	4	Feb 24	TEMA now available on STN
NEWS	5	Feb 26	NTIS now allows simultaneous left and right truncation
NEWS	6	Feb 26	PCTFULL now contains images
NEWS	7	Mar 04	SDI PACKAGE for monthly delivery of multifile SDI results
NEWS	8	Mar 24	PATDPAFULL now available on STN
NEWS	9	Mar 24	Additional information for trade-named substances without structures available in REGISTRY
NEWS	10	Apr 11	Display formats in DGENE enhanced
NEWS	11	Apr 14	MEDLINE Reload
NEWS	12	Apr 17	Polymer searching in REGISTRY enhanced
NEWS	13	Jun 13	Indexing from 1947 to 1956 added to records in CA/CAPLUS
NEWS	14	Apr 21	New current-awareness alert (SDI) frequency in WPIDS/WPINDEX/WPIX
NEWS	15	Apr 28	RDISCLOSURE now available on STN
NEWS	16	May 05	Pharmacokinetic information and systematic chemical names added to PHAR
NEWS	17	May 15	MEDLINE file segment of TOXCENTER reloaded
NEWS	18	May 15	Supporter information for ENCOMPPAT and ENCOMPLIT updated
NEWS	19	May 19	Simultaneous left and right truncation added to WSCA
NEWS	20	May 19	RAPRA enhanced with new search field, simultaneous left and right truncation
NEWS	21	Jun 06	Simultaneous left and right truncation added to CBNB
NEWS	22	Jun 06	PASCAL enhanced with additional data
NEWS	23	Jun 20	2003 edition of the FSTA Thesaurus is now available
NEWS	24	Jun 25	HSDB has been reloaded
NEWS	25	Jul 16	Data from 1960-1976 added to RDISCLOSURE
NEWS	26	Jul 21	Identification of STN records implemented
NEWS	27	Jul 21	Polymer class term count added to REGISTRY
NEWS	28	Jul 22	INPADOC: Basic index (/BI) enhanced; Simultaneous Left and Right Truncation available
NEWS	29	AUG 05	New pricing for EUROPATFULL and PCTFULL effective August 1, 2003
NEWS EXPRESS			April 4 CURRENT WINDOWS VERSION IS V6.01a, CURRENT MACINTOSH VERSION IS V6.0b(ENG) AND V6.0Jb(JP), AND CURRENT DISCOVER FILE IS DATED 01 APRIL 2003
NEWS HOURS			STN Operating Hours Plus Help Desk Availability
NEWS INTER			General Internet Information
NEWS LOGIN			Welcome Banner and News Items
NEWS PHONE			Direct Dial and Telecommunication Network Access to STN
NEWS WWW			CAS World Wide Web Site (general information)

Enter NEWS followed by the item number or name to see news on that

.specific topic.

All use of STN is subject to the provisions of the STN Customer agreement. Please note that this agreement limits use to scientific research. Use for software development or design or implementation of commercial gateways or other similar uses is prohibited and may result in loss of user privileges and other penalties.

\* \* \* \* \* STN Columbus \* \* \* \* \*

FILE 'HOME' ENTERED AT 17:39:51 ON 09 AUG 2003

=> registry

THIS COMMAND NOT AVAILABLE IN THE CURRENT FILE

Some commands only work in certain files. For example, the EXPAND command can only be used to look at the index in a file which has an index. Enter "HELP COMMANDS" at an arrow prompt (=>) for a list of commands which can be used in this file.

=> file registry

COST IN U.S. DOLLARS	SINCE FILE ENTRY	TOTAL SESSION
FULL ESTIMATED COST	0.21	0.21

FILE 'REGISTRY' ENTERED AT 17:40:08 ON 09 AUG 2003

USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT.

PLEASE SEE "HELP USAGETERMS" FOR DETAILS.

COPYRIGHT (C) 2003 American Chemical Society (ACS)

Property values tagged with IC are from the ZIC/VINITI data file provided by InfoChem.

STRUCTURE FILE UPDATES: 8 AUG 2003 HIGHEST RN 563538-18-1

DICTIONARY FILE UPDATES: 8 AUG 2003 HIGHEST RN 563538-18-1

TSCA INFORMATION NOW CURRENT THROUGH JANUARY 6, 2003

Please note that search-term pricing does apply when conducting SmartSELECT searches.

Crossover limits have been increased. See HELP CROSSOVER for details.

Experimental and calculated property data are now available. See HELP PROPERTIES for more information. See STNote 27, Searching Properties in the CAS Registry File, for complete details:

<http://www.cas.org/ONLINE/STN/STNOTES/stnotes27.pdf>

=> e potassium stannate

E1	1	POTASSIUM/BI
E2	106000	POTASSIUM/BI
E3	0 -->	POTASSIUM STANNATE/BI
E4	1	POTASSIUMAZIRIDINE/BI
E5	2	POTASSIUMHEXA/BI
E6	1	POTASSIUMHEXACHLORO/BI
E7	1	POTASSIUMHEXACHLOROMOLYBD/BI
E8	1	POTASSIUMHEXACHLOROMOLYBD/BI
E9	1	POTASSIUMHEXAFLUORO/BI
E10	1	POTASSIUMHEXAFLUOROCER/BI
E11	1	POTASSIUMHEXAFLUOROCERATE/BI
E12	1	POTASSIUMMYRIST/BI

=> e sodium stannate

E1 1 SODIUM/BI  
 E2 273934 SODIUM/BI  
 E3 0 --> SODIUM STANNATE/BI  
 E4 9 SODIUM:ALANINE/BI  
 E5 1 SODIUM:CHOLATE/BI  
 E6 1 SODIUM:CITRATE/BI  
 E7 17 SODIUM:DICARBOXYLATE/BI  
 E8 6 SODIUM:GALACTOSIDE/BI  
 E9 1 SODIUM:GLUTAMATE/BI  
 E10 1 SODIUM:NEUROTRANSMITTER/BI  
 E11 2 SODIUM:PANTOTHENATE/BI  
 E12 6 SODIUM:PROLINE/BI

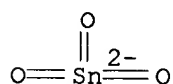
=> ammonium stannate  
 79013 AMMONIUM  
 7694 STANNATE  
 L1 1 AMMONIUM STANNATE  
 (AMMONIUM(W) STANNATE)

=> d, all  
 3922588 D  
 18193 ALL  
 L2 26 D, ALL  
 (D(W)ALL)

=> d, 11,all  
 3922588 D  
 0 L1,ALL  
 L3 0 D, L1,ALL  
 (D(W)L1,ALL)

=> d 11

L1 ANSWER 1 OF 1 REGISTRY COPYRIGHT 2003 ACS on STN  
 RN 111716-23-5 REGISTRY  
 CN Stannate (SnO32-), diammonium (9CI) (CA INDEX NAME)  
 OTHER CA INDEX NAMES:  
 CN **Ammonium stannate(IV) ((NH4)2SnO3) (6CI)**  
 MF H4 N . 1/2 O3 Sn  
 CI CCS  
 SR CA  
 LC STN Files: CA, CAOLD, CAPLUS, USPATFULL  
 CRN (38668-37-0)



●2 NH<sub>4</sub><sup>+</sup>

6 REFERENCES IN FILE CA (1947 TO DATE)  
 6 REFERENCES IN FILE CAPLUS (1947 TO DATE)  
 1 REFERENCES IN FILE CAOLD (PRIOR TO 1967)

=> s calplus  
 L4 1 CALPLUS



DT Patent  
 LA English  
 IC ICM B24B001-00  
 NCL 451041000  
 CC 76-3 (Electric Phenomena)  
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2002031985	A1	20020314	US 2001-842476	20010425
PRAI	US 2000-221603P	P	20000728		
AB	A method and compn. with long pot life for CMP planarizing a substrate surface is provided. The polishing compn. includes an oxidizer capable of oxidizing a metal undergoing planarization and yielding a complexing agent which complexes with the oxidized metal and a stabilizer such as a stannate salt. The compn. may further include abrasive particles and/or inhibitors. The compn. may be used in a multi-step polishing process including polishing a substrate surface to selectively remove a metal layer with respect to a barrier layer and dielec. layer and polishing a substrate surface using the compn. to nonselectively remove the metal layer, a barrier layer, and a dielec. layer from the substrate surface.				
ST	CMP slurry dielec metal film electronics				
IT	Abrasives Alkyl groups Aryl groups Complexing agents Corrosion inhibitors Dielectric films Diffusion barrier Oxidizing agents Particles Slurries Stabilizing agents (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)				
IT	Metals, processes RL: CPS (Chemical process); PEP (Physical, engineering or chemical process); REM (Removal or disposal); TEM (Technical or engineered material use); PROC (Process); USES (Uses) (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)				
IT	Carboxylic acids, uses Polyoxyalkylenes, uses RL: TEM (Technical or engineered material use); USES (Uses) (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)				
IT	Polishing (chem.-mech.; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)				
IT	Polyoxyalkylenes, uses RL: TEM (Technical or engineered material use); USES (Uses) (derivs.; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)				
IT	Polyoxyalkylenes, uses RL: TEM (Technical or engineered material use); USES (Uses) (peroxy acid derivs.; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)				
IT	Carboxylic acids, uses RL: TEM (Technical or engineered material use); USES (Uses) (peroxy; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)				
IT	Functional groups (peroxycarboxylate; chem. mech. polishing compn. with long pot life for				

smoothing metal layers for electronic devices)

IT Carboxylic acids, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (salts; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT 334490-97-0, Black diamond  
 RL: CPS (Chemical process); PEP (Physical, engineering or chemical process); REM (Removal or disposal); TEM (Technical or engineered material use); PROC (Process); USES (Uses)  
 (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT 7440-25-7, Tantalum, processes 7440-31-5D, Tin, salts 7440-50-8, Copper, processes  
 RL: CPS (Chemical process); PEP (Physical, engineering or chemical process); TEM (Technical or engineered material use); PROC (Process); USES (Uses)  
 (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT 51-17-2, Benzimidazole 71-43-2, Benzene, uses 71-43-2D, Benzene, derivs. 79-21-0, Peroxyacetic acid 93-59-4, Peroxybenzoic acid 95-14-7, 1H-Benzotriazole 95-16-9, Benzothiazole 107-32-4, Peroxyformic acid 288-32-4, Imidazole, uses 1310-58-3, Potassium hydroxide, uses 1336-21-6, Ammonium hydroxide 12058-66-1, Sodium stannate 12142-33-5, Potassium stannate 25322-68-3, Polyethylene glycol 25322-68-3D, Polyethylene glycol, derivs. 25322-68-3D, Polyethylene glycol, peroxic acid derivs. 26264-09-5, Chlorobenzoic acid 28804-48-0, Mercaptobenzotriazole **111716-23-5** 403855-40-3  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT 7631-86-9, Colloidal silica, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (colloidal; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT 7440-44-0, Carbon, uses  
 RL: MOA (Modifier or additive use); USES (Uses)  
 (silica dopant; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

=> d,l6,kwic  
 2011232 D  
 3101 'L6'  
 46 KWIC  
 L8 0 D,L6,KWIC  
 (D(W)'L6'(W)KWIC)

=> s 111716-23-5 and (chemical mechanical polishing)

**REGISTRY INITIATED**

Substance data SEARCH and crossover from CAS REGISTRY in progress...  
 Use DISPLAY HITSTR (or FHITSTR) to directly view retrieved structures.

L10 6 L9

815474 CHEMICAL  
 229418 MECHANICAL

41510 POLISHING  
 1426 CHEMICAL MECHANICAL POLISHING  
 (CHEMICAL(W)MECHANICAL(W)POLISHING)  
 L11 1 L10 AND (CHEMICAL MECHANICAL POLISHING)

=> d l11,all

L11 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2003 ACS on STN  
 AN 2002:185682 CAPLUS  
 DN 136:255652  
 TI **Chemical mechanical polishing** composition  
 with long pot life for smoothing metal layers for electronic devices  
 IN Wang, Yuchun; Bajaj, Rajeev; Redeker, Fred C.; Li, Shijian  
 PA Applied Materials, Inc., USA  
 SO U.S. Pat. Appl. Publ., 12 pp.  
 CODEN: USXXCO  
 DT Patent  
 LA English  
 IC ICM B24B001-00  
 NCL 451041000  
 CC 76-3 (Electric Phenomena)  
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
	-----	---	-----	-----	-----
PI	US 2002031985	A1	20020314	US 2001-842476	20010425
PRAI	US 2000-221603P	P	20000728		
AB	A method and compn. with long pot life for CMP planarizing a substrate surface is provided. The polishing compn. includes an oxidizer capable of oxidizing a metal undergoing planarization and yielding a complexing agent which complexes with the oxidized metal and a stabilizer such as a stannate salt. The compn. may further include abrasive particles and/or inhibitors. The compn. may be used in a multi-step polishing process including polishing a substrate surface to selectively remove a metal layer with respect to a barrier layer and dielec. layer and polishing a substrate surface using the compn. to nonselectively remove the metal layer, a barrier layer, and a dielec. layer from the substrate surface.				
ST	CMP slurry dielec metal film electronics				
IT	Abrasives Alkyl groups Aryl groups Complexing agents Corrosion inhibitors Dielectric films Diffusion barrier Oxidizing agents Particles Slurries Stabilizing agents (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)				
IT	Metals, processes RL: CPS (Chemical process); PEP (Physical, engineering or chemical process); REM (Removal or disposal); TEM (Technical or engineered material use); PROC (Process); USES (Uses) (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)				
IT	Carboxylic acids, uses Polyoxyalkylenes, uses RL: TEM (Technical or engineered material use); USES (Uses) (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)				

IT Polishing  
 (chem.-mech.; chem. mech. polishing compn. with long pot life for  
 smoothing metal layers for electronic devices)

IT Polyoxyalkylenes, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (derivs.; chem. mech. polishing compn. with long pot life for smoothing  
 metal layers for electronic devices)

IT Polyoxyalkylenes, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (peroxic acid derivs.; chem. mech. polishing compn. with long pot life  
 for smoothing metal layers for electronic devices)

IT Carboxylic acids, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (peroxy; chem. mech. polishing compn. with long pot life for smoothing  
 metal layers for electronic devices)

IT Functional groups  
 (peroxycarboxylate; chem. mech. polishing compn. with long pot life for  
 smoothing metal layers for electronic devices)

IT Carboxylic acids, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (salts; chem. mech. polishing compn. with long pot life for smoothing  
 metal layers for electronic devices)

IT 334490-97-0, Black diamond  
 RL: CPS (Chemical process); PEP (Physical, engineering or chemical  
 process); REM (Removal or disposal); TEM (Technical or engineered material  
 use); PROC (Process); USES (Uses)  
 (chem. mech. polishing compn. with long pot life for smoothing metal  
 layers for electronic devices)

IT 7440-25-7, Tantalum, processes 7440-31-5D, Tin, salts 7440-50-8,  
 Copper, processes  
 RL: CPS (Chemical process); PEP (Physical, engineering or chemical  
 process); TEM (Technical or engineered material use); PROC (Process); USES  
 (Uses)  
 (chem. mech. polishing compn. with long pot life for smoothing metal  
 layers for electronic devices)

IT 51-17-2, Benzimidazole 71-43-2, Benzene, uses 71-43-2D, Benzene,  
 derivs. 79-21-0, Peroxyacetic acid 93-59-4, Peroxybenzoic acid  
 95-14-7, 1H-Benzotriazole 95-16-9, Benzothiazole 107-32-4,  
 Peroxyformic acid 288-32-4, Imidazole, uses 1310-58-3, Potassium  
 hydroxide, uses 1336-21-6, Ammonium hydroxide 12058-66-1, Sodium  
 stannate 12142-33-5, Potassium stannate 25322-68-3, Polyethylene  
 glycol 25322-68-3D, Polyethylene glycol, derivs. 25322-68-3D,  
 Polyethylene glycol, peroxic acid derivs. 26264-09-5, Chlorobenzoic acid  
 28804-48-0, Mercaptobenzotriazole **111716-23-5** 403855-40-3  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (chem. mech. polishing compn. with long pot life for smoothing metal  
 layers for electronic devices)

IT 7631-86-9, Colloidal silica, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (colloidal; chem. mech. polishing compn. with long pot life for  
 smoothing metal layers for electronic devices)

IT 7440-44-0, Carbon, uses  
 RL: MOA (Modifier or additive use); USES (Uses)  
 (silica dopant; chem. mech. polishing compn. with long pot life for  
 smoothing metal layers for electronic devices)

=> s (chemical mechanical polishing) and ((sodium stannate) or (potassium stannate)  
 or (ammonium stannate))

815474 CHEMICAL  
 229418 MECHANICAL  
 41510 POLISHING



1426 CHEMICAL MECHANICAL POLISHING  
 (CHEMICAL(W)MECHANICAL(W) POLISHING)  
 885255 SODIUM  
 3785 STANNATE  
 389 SODIUM STANNATE  
 (SODIUM(W) STANNATE)  
 509299 POTASSIUM  
 3785 STANNATE  
 112 POTASSIUM STANNATE  
 (POTASSIUM(W) STANNATE)  
 313608 AMMONIUM  
 3785 STANNATE  
 13 AMMONIUM STANNATE  
 (AMMONIUM(W) STANNATE)  
 L12 1 (CHEMICAL MECHANICAL POLISHING) AND ((SODIUM STANNATE) OR (POTASSIUM STANNATE) OR (AMMONIUM STANNATE))

=> d, 112, all  
 2011232 D  
 3624 'L12'  
 1671310 ALL  
 L13 0 D, L12, ALL  
 (D(W) 'L12' (W) ALL)

=> d 112,all

L12 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2003 ACS on STN  
 AN 2002:185682 CAPLUS  
 DN 136:255652  
 TI **Chemical mechanical polishing** composition  
 with long pot life for smoothing metal layers for electronic devices  
 IN Wang, Yuchun; Bajaj, Rajeev; Redeker, Fred C.; Li, Shijian  
 PA Applied Materials, Inc., USA  
 SO U.S. Pat. Appl. Publ., 12 pp.  
 CODEN: USXXCO  
 DT Patent  
 LA English  
 IC ICM B24B001-00  
 NCL 451041000  
 CC 76-3 (Electric Phenomena)  
 FAN.CNT 1

*Inventors*  
*same as*  
*09/842 476*

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2002031985	A1	20020314	US 2001-842476	20010425
PRAI	US 2000-221603P	P	20000728		
AB	A method and compn. with long pot life for CMP planarizing a substrate surface is provided. The polishing compn. includes an oxidizer capable of oxidizing a metal undergoing planarization and yielding a complexing agent which complexes with the oxidized metal and a stabilizer such as a stannate salt. The compn. may further include abrasive particles and/or inhibitors. The compn. may be used in a multi-step polishing process including polishing a substrate surface to selectively remove a metal layer with respect to a barrier layer and dielec. layer and polishing a substrate surface using the compn. to nonselectively remove the metal layer, a barrier layer, and a dielec. layer from the substrate surface.				
ST	CMP slurry dielec metal film electronics				
IT	Abrasives Alkyl groups Aryl groups Complexing agents Corrosion inhibitors Dielectric films				

Diffusion barrier  
 Oxidizing agents  
 Particles  
 Slurries  
 Stabilizing agents  
 (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT Metals, processes  
 RL: CPS (Chemical process); PEP (Physical, engineering or chemical process); REM (Removal or disposal); TEM (Technical or engineered material use); PROC (Process); USES (Uses)  
 (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT Carboxylic acids, uses  
 Polyoxyalkylenes, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT Polishing  
 (chem.-mech.; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT Polyoxyalkylenes, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (derivs.; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT Polyoxyalkylenes, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (peroxic acid derivs.; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT Carboxylic acids, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (peroxy; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT Functional groups  
 (peroxycarboxylate; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT Carboxylic acids, uses  
 RL: TEM (Technical or engineered material use); USES (Uses)  
 (salts; chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT 334490-97-0, Black diamond  
 RL: CPS (Chemical process); PEP (Physical, engineering or chemical process); REM (Removal or disposal); TEM (Technical or engineered material use); PROC (Process); USES (Uses)  
 (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT 7440-25-7, Tantalum, processes 7440-31-5D, Tin, salts 7440-50-8, Copper, processes  
 RL: CPS (Chemical process); PEP (Physical, engineering or chemical process); TEM (Technical or engineered material use); PROC (Process); USES (Uses)  
 (chem. mech. polishing compn. with long pot life for smoothing metal layers for electronic devices)

IT 51-17-2, Benzimidazole 71-43-2, Benzene, uses 71-43-2D, Benzene, derivs. 79-21-0, Peroxyacetic acid 93-59-4, Peroxybenzoic acid 95-14-7, 1H-Benzotriazole 95-16-9, Benzothiazole 107-32-4, Peroxyformic acid 288-32-4, Imidazole, uses 1310-58-3, Potassium hydroxide, uses 1336-21-6, Ammonium hydroxide 12058-66-1, **Sodium stannate** 12142-33-5, **Potassium stannate** 25322-68-3, Polyethylene glycol 25322-68-3D, Polyethylene glycol, derivs. 25322-68-3D, Polyethylene glycol, peroxic acid derivs. 26264-09-5, Chlorobenzoic acid 28804-48-0,

• Mercaptobenzotriazole 111716-23-5 403855-40-3  
RL: TEM (Technical or engineered material use); USES (Uses)  
(chem. mech. polishing compn. with long pot life for smoothing metal  
layers for electronic devices)  
IT 7631-86-9, Colloidal silica, uses  
RL: TEM (Technical or engineered material use); USES (Uses)  
(colloidal; chem. mech. polishing compn. with long pot life for  
smoothing metal layers for electronic devices)  
IT 7440-44-0, Carbon, uses  
RL: MOA (Modifier or additive use); USES (Uses)  
(silica dopant; chem. mech. polishing compn. with long pot life for  
smoothing metal layers for electronic devices)